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(54) **LIQUID CRYSTAL DISPLAY DEVICE**

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1/136286 (2013.01); **G02F 2001/134345**
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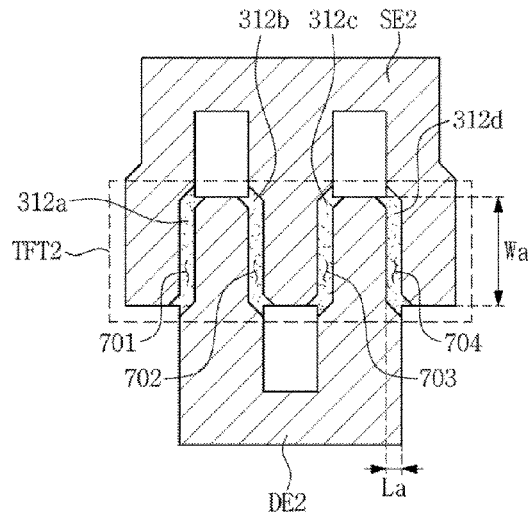
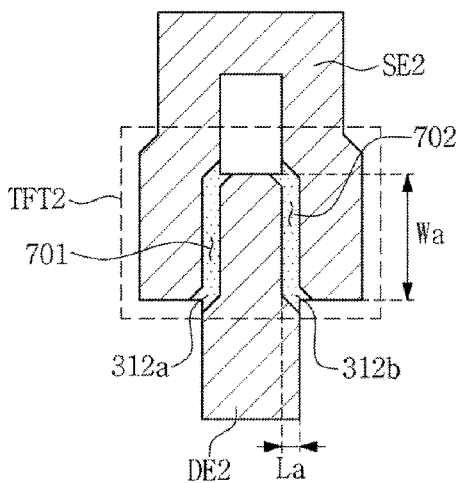
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(57) **ABSTRACT**

A liquid crystal display (“LCD”) device capable of easily setting up an accurate resistance ratio between thin film transistors, the LCD device includes a first substrate including a gate line and a data line, a second substrate opposing the first substrate, a liquid crystal layer between the first substrate and the second substrate, a first sub-pixel electrode in a first sub-pixel region of the first substrate, a second sub-pixel electrode in a second sub-pixel region of the first substrate, a first transistor connected to the gate line, the data line, and the first sub-pixel electrode, a second transistor connected to the gate line, the first transistor, and the second sub-pixel electrode, and a third transistor connected to the gate line, the second sub-pixel electrode, and a storage line, wherein one of the first, second, and third transistors includes a plurality of divided channel regions.

10 Claims, 15 Drawing Sheets



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FIG. 2

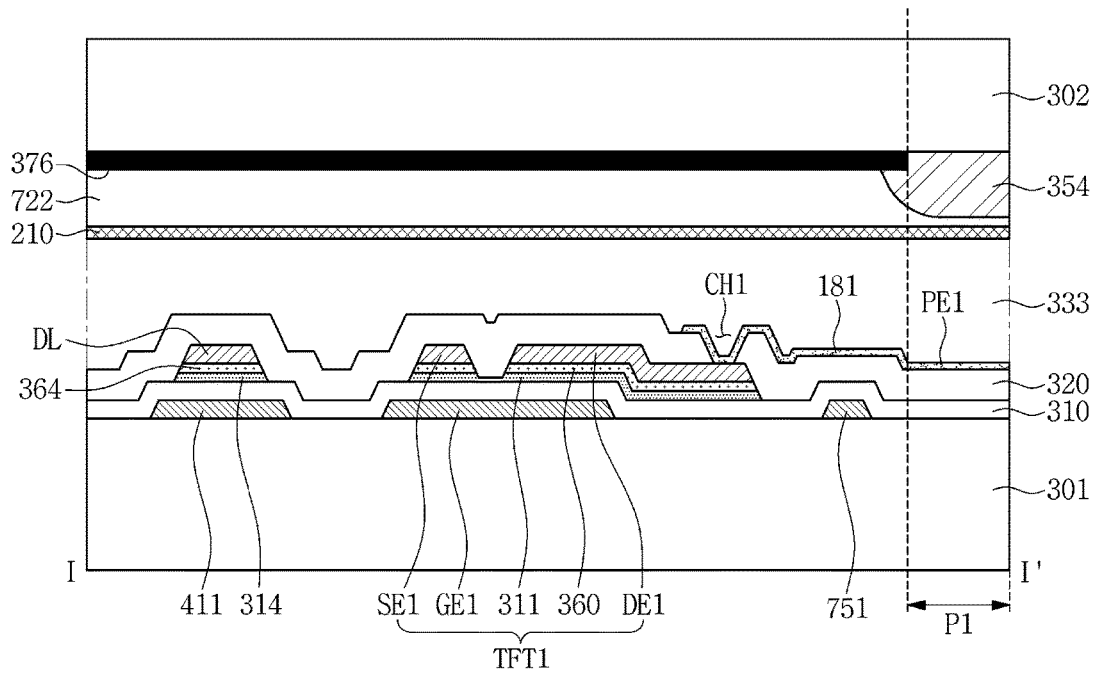


FIG. 3

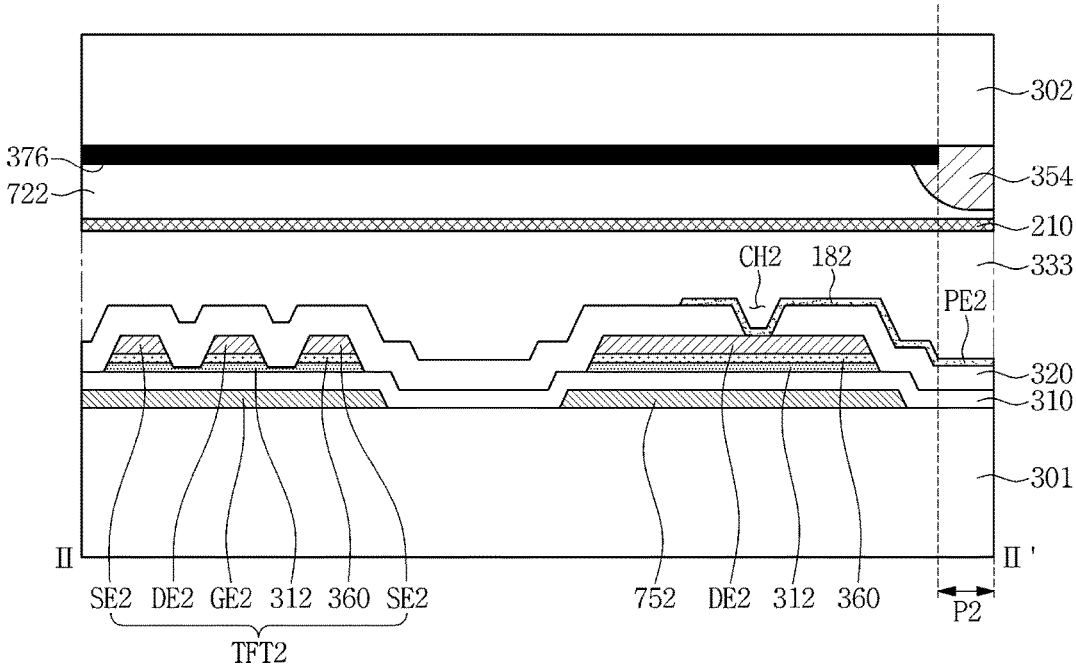


FIG. 5

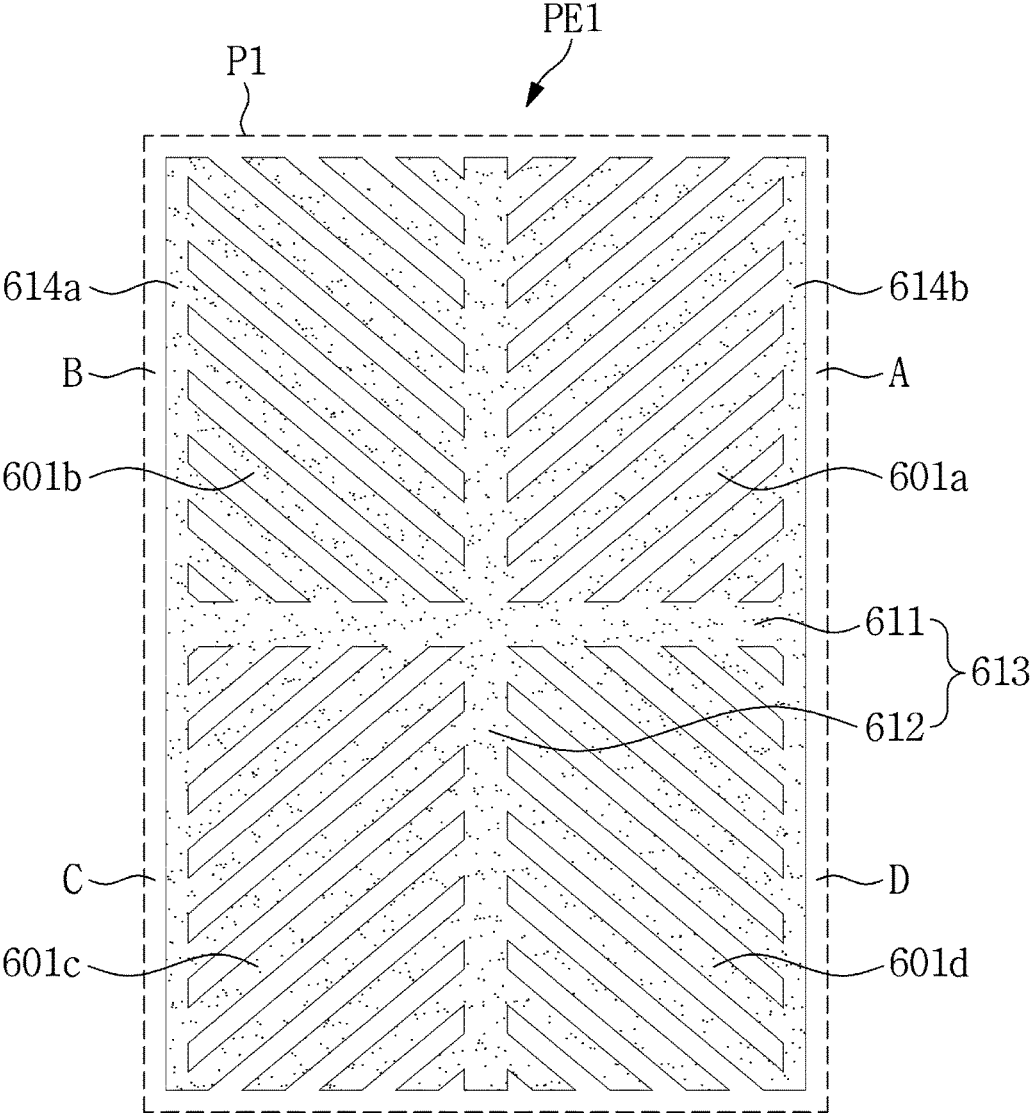


FIG. 6

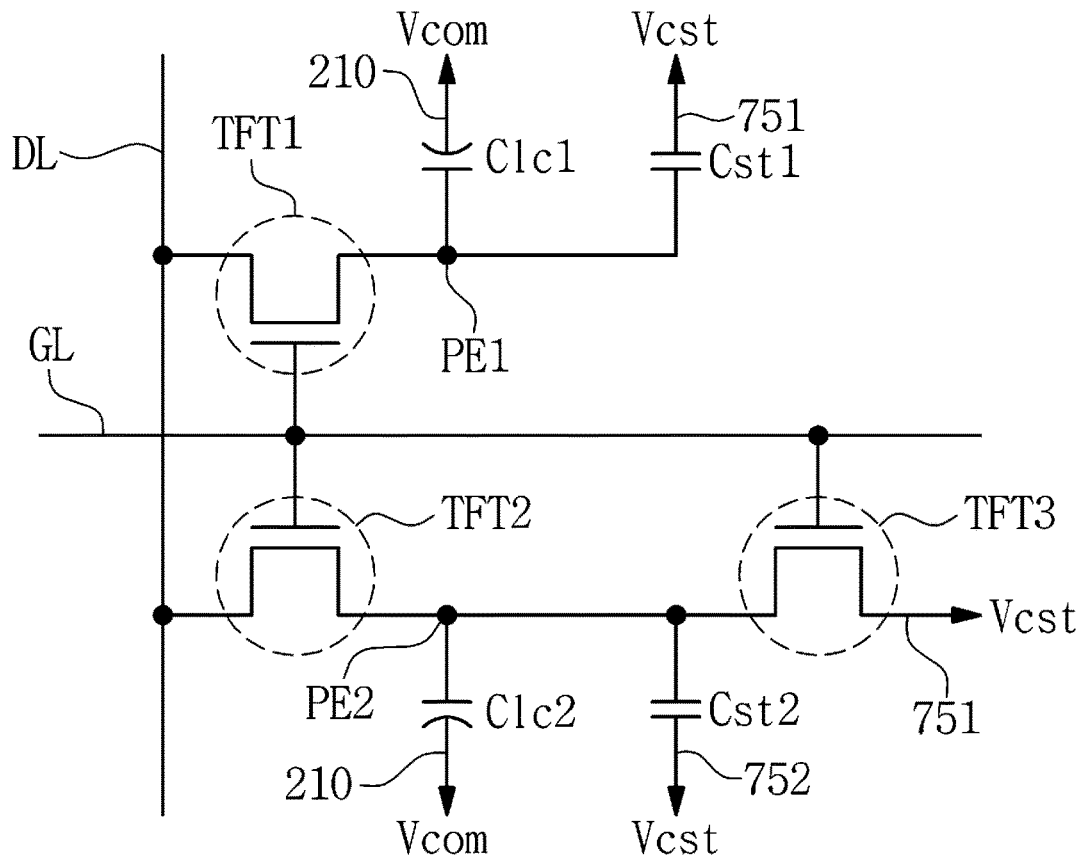


FIG. 7A

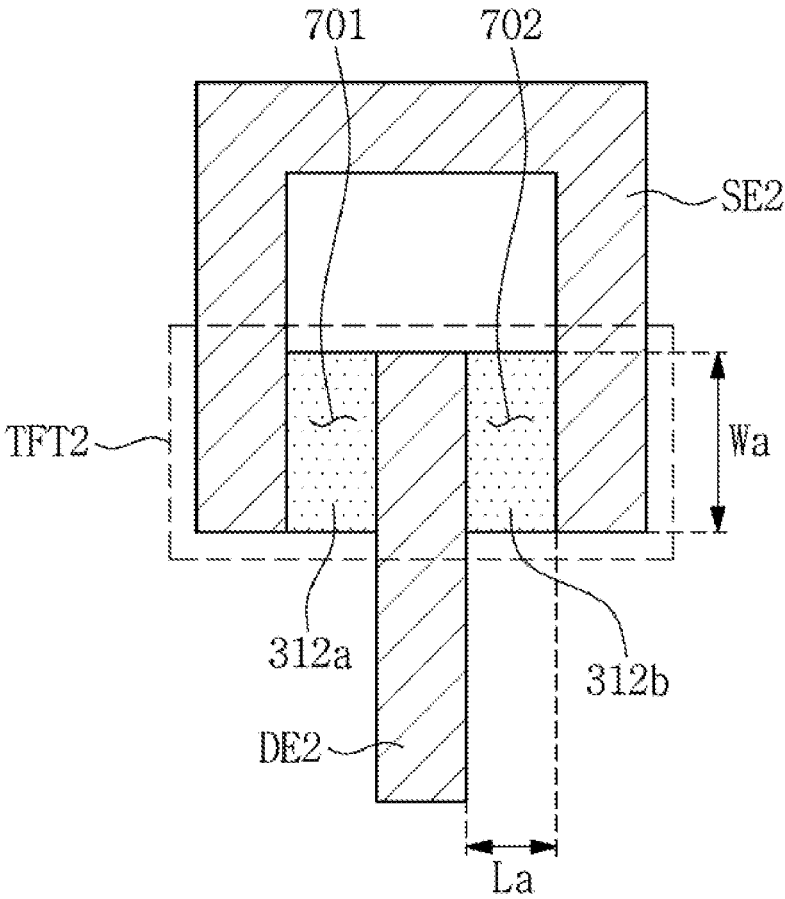


FIG. 7B

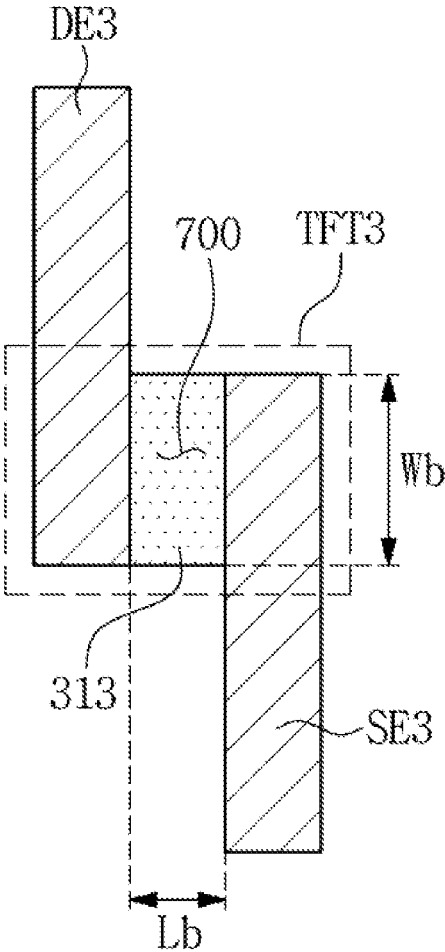


FIG. 8A

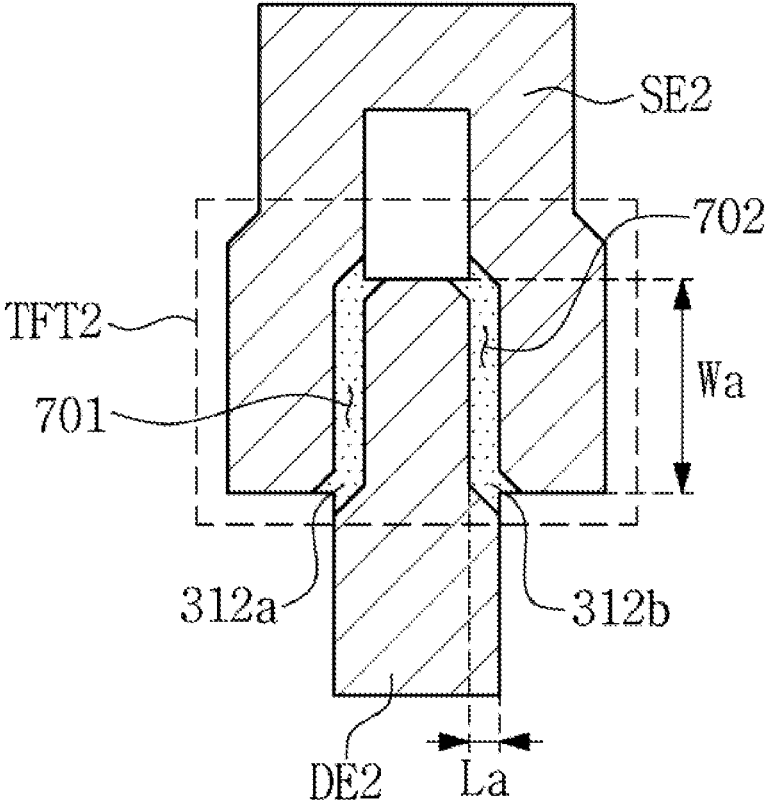


FIG. 8B

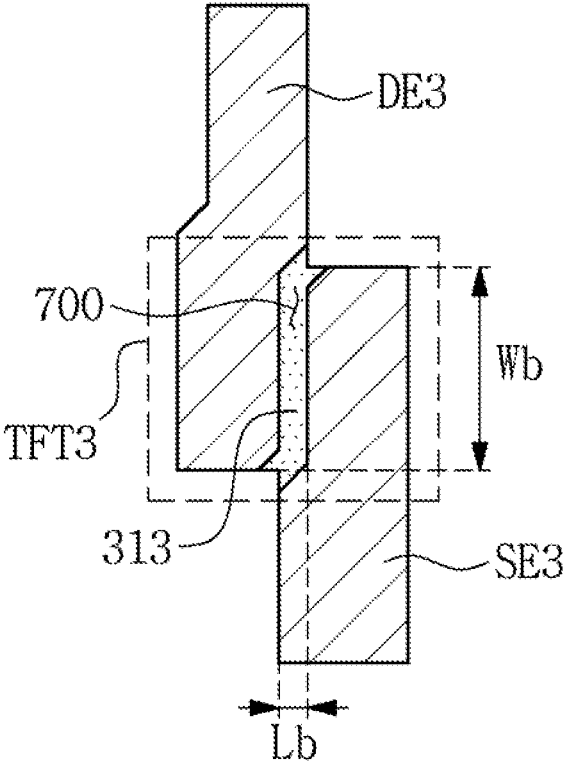


FIG. 9B

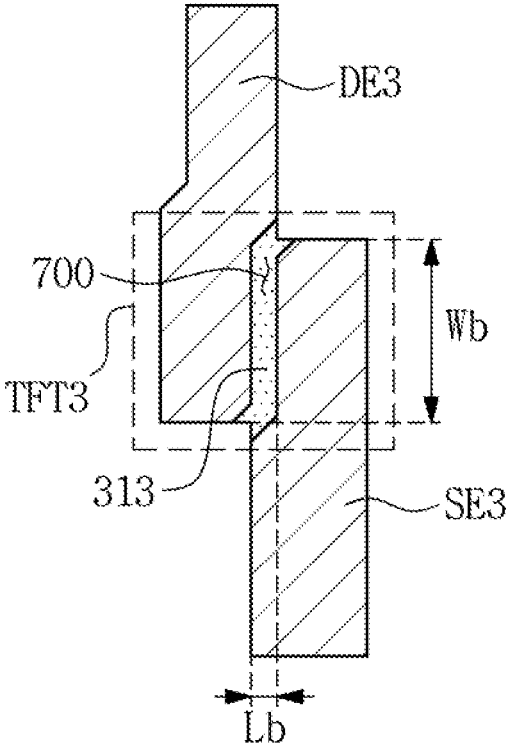


FIG. 10A

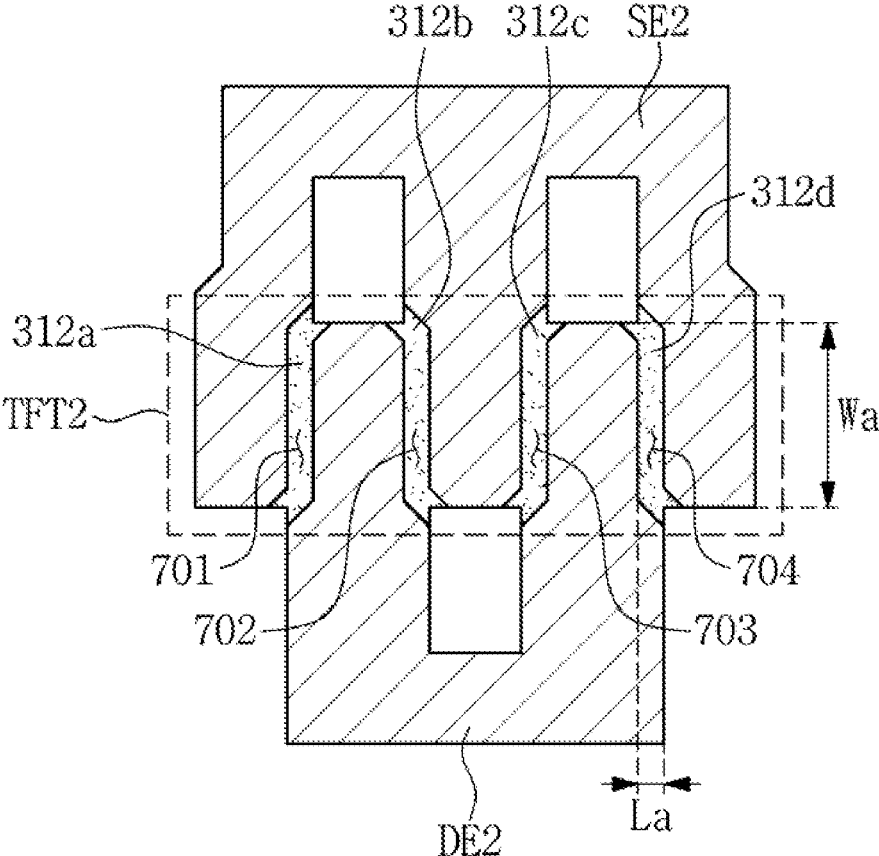


FIG. 10B

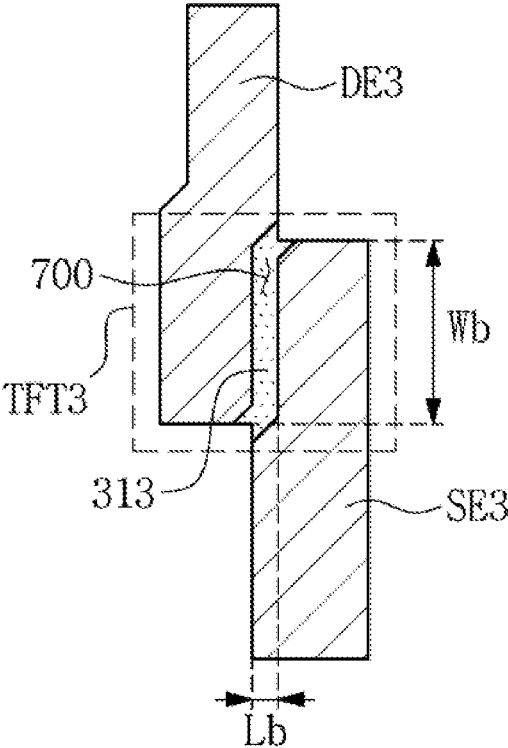


FIG. 11

	TFT3	TFT2'	TFT2
$W_{\min} [\mu\text{m}]$	4.89	23.39	17.40
$W_{\max} [\mu\text{m}]$	6.10	24.43	20.04
$\Delta W [\mu\text{m}]$	1.21	1.04	2.64
RATIO	1.00	0.86	2.18

LIQUID CRYSTAL DISPLAY DEVICE

This application claims priority to Korean Patent Application No. 10-2015-0060623, filed on Apr. 29, 2015, and all the benefits accruing therefrom under 35 U.S.C. §119, the content of which in its entirety is incorporated herein by reference.

BACKGROUND**1. Field**

Embodiments of the invention relate to a liquid crystal display (“LCD”) device, and more particularly, to an LCD device capable of easily setting up an accurate resistance ratio between thin film transistors.

2. Description of the Related Art

A liquid crystal display (“LCD”) device is a type of flat panel display (“FPD”) device which has been widely used recently. An LCD device generally includes two substrates having electrodes formed thereon and a liquid crystal layer interposed therebetween.

In such an LCD device, liquid crystal molecules of the liquid crystal layer are rearranged upon voltages being applied to the two electrodes, and thereby an amount of transmitted light is adjusted in the LCD device.

To enhance visibility, a single pixel may include two individual sub-pixel electrodes. In this case, data signals having different values need to be applied to the respective sub-pixel electrodes through a single data line. Therefore, a data signal which is unmodulated may be applied to one of the sub-pixel electrodes, and the data signal may be divided to be applied to the other sub-pixel electrode.

Since the pixel having the above-described structure includes two transistors having different internal resistance levels, a data voltage may be divided by the two transistors.

As a resolution of a display device increases, a size of the transistor may be inevitably reduced. Accordingly, one of the two transistors may have a channel region which allows a size of the transistor to be significantly reduced.

SUMMARY

As one of the two transistors has a channel having a different shape from that of the other transistor as described above, predicting a resistance ratio between the transistors may be difficult. In this regard, the design and manufacture of the transistors may be complicated. In a case in which the transistors are not manufactured based on an accurate resistance ratio, an actual ratio between levels of voltages applied to the two sub-pixel electrodes may be distorted, as compared to the predetermined ratio, thus resulting in the degradation of image quality.

Exemplary embodiments of embodiments of the invention are directed to a liquid crystal display (“LCD”) device capable of easily setting up an accurate resistance ratio between transistors.

According to an exemplary embodiment of the invention, an LCD device includes a first substrate comprising a gate line and a data line, a second substrate opposing the first substrate, a liquid crystal layer between the first substrate and the second substrate, a first sub-pixel electrode in a first sub-pixel region of the first substrate, a second sub-pixel electrode in a second sub-pixel region of the first substrate, a first transistor connected to the gate line, the data line, and the first sub-pixel electrode, a second transistor connected to the gate line, the first transistor, and the second sub-pixel electrode, and a third transistor connected to the gate line,

the second sub-pixel electrode, and a storage line, wherein one of the first, second, and third transistors includes a plurality of divided channel regions.

In an exemplary embodiment, the number of channel regions of one of the transistors may be “n” times (“n” being a natural number) greater than the number of channel regions of another of the transistors.

In an exemplary embodiment, one of the transistors may be the second transistor, and another of the transistors is the third transistor.

In an exemplary embodiment, one of the transistors may be the second transistor.

In an exemplary embodiment, the first transistor may include a same number of channel regions as a number of channel regions of the third transistor.

In an exemplary embodiment, a source electrode and a drain electrode included in one of the transistors may have a same number of protrusions.

In an exemplary embodiment, a total area of the channel regions included in the second transistor may be greater than an area of the channel region included in the third transistor.

In an exemplary embodiment, one of the channel regions of the second transistor may have a same shape and an area as a shape and an area of the channel region of the third transistor.

In an exemplary embodiment, respective end portions of a source electrode and a drain electrode facing one another of at least one of the first, second, and third transistors may have a curved shape.

In an exemplary embodiment, the end portion of the source electrode and the end portion of the drain electrode may each include a plurality of sides having different lengths.

In an exemplary embodiment, the end portion of the source electrode and the end portion of the drain electrode may each include sides having different lengths at respective corresponding positions.

In an exemplary embodiment, the end portion of the source electrode may have a same length as a length of the end portion of the drain electrode facing one another.

The foregoing is illustrative only and is not intended to be in any way limiting. In addition to the illustrative exemplary embodiments, embodiments, and features described above, further exemplary embodiments, embodiments, and features will become apparent by reference to the drawings and the following detailed description.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other features and exemplary embodiments of the invention will be more clearly understood from the following detailed description taken in conjunction with the accompanying drawings, in which:

FIG. 1 is a plan view illustrating an exemplary embodiment of a pixel according to the invention;

FIG. 2 is a cross-sectional view taken along line I-I' of FIG. 1;

FIG. 3 is a cross-sectional view taken along line II-II' of FIG. 1;

FIG. 4 is a cross-sectional view taken along line III-III' of FIG. 1;

FIG. 5 is a view illustrating a sub-pixel electrode of FIG. 1;

FIG. 6 is an equivalent circuit schematic of the pixel illustrated in FIG. 1;

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FIGS. 7A and 7B are views illustrating an exemplary embodiment of a structure of a second thin film transistor (“TFT”) and a third TFT of FIG. 1;

FIGS. 8A and 8B are views illustrating another exemplary embodiment of the structure of the second TFT and the third TFT of FIG. 1;

FIGS. 9A and 9B are views illustrating still another exemplary embodiment of the structure of the second TFT and the third TFT of FIG. 1;

FIGS. 10A and 10B are views illustrating yet another exemplary embodiment of the structure of the second TFT and the third TFT of FIG. 1; and

FIG. 11 is a view illustrating effects of the exemplary embodiment.

DETAILED DESCRIPTION

Advantages and features of the invention and methods for achieving them will be made clear from exemplary embodiments described below in detail with reference to the accompanying drawings. The invention may, however, be embodied in many different forms and should not be construed as being limited to the exemplary embodiments set forth herein. Rather, these exemplary embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art. The invention is merely defined by the scope of the claims. Therefore, well-known constituent elements, operations and techniques are not described in detail in the exemplary embodiments in order to prevent the invention from being obscurely interpreted. Like reference numerals refer to like elements throughout the specification.

In the drawings, thicknesses of a plurality of layers and areas are illustrated in an enlarged manner for clarity and ease of description thereof. When a layer, area, or plate is referred to as being “on” another layer, area, or plate, it may be directly on the other layer, area, or plate, or intervening layers, areas, or plates may be present therebetween. Conversely, when a layer, area, or plate is referred to as being “directly on” another layer, area, or plate, intervening layers, areas, or plates may be absent therebetween. Further when a layer, area, or plate is referred to as being “below” another layer, area, or plate, it may be directly below the other layer, area, or plate, or intervening layers, areas, or plates may be present therebetween. Conversely, when a layer, area, or plate is referred to as being “directly below” another layer, area, or plate, intervening layers, areas, or plates may be absent therebetween.

The spatially relative terms “below”, “beneath”, “lower”, “above”, “upper”, and the like, may be used herein for ease of description to describe the relations between one element or component and another element or component as illustrated in the drawings. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation, in addition to the orientation depicted in the drawings. For example, in the case where a device shown in the drawing is turned over, the device positioned “below” or “beneath” another device may be placed “above” another device. Accordingly, the illustrative term “below” may include both the lower and upper positions. The device may also be oriented in the other direction, and thus the spatially relative terms may be interpreted differently depending on the orientations.

Throughout the specification, when an element is referred to as being “connected” to another element, the element is “directly connected” to the other element, or “electrically connected” to the other element with one or more interven-

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ing elements interposed therebetween. It will be further understood that the terms “comprises,” “comprising,” “includes” and/or “including,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

It will be understood that, although the terms “first,” “second,” “third,” and the like may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one element from another element. Thus, “a first element” discussed below could be termed “a second element” or “a third element,” and “a second element” and “a third element” can be termed likewise without departing from the teachings herein.

Furthermore, relative terms, such as “lower” or “bottom” and “upper” or “top,” may be used herein to describe one element’s relationship to another element as illustrated in the Figures. It will be understood that relative terms are intended to encompass different orientations of the device in addition to the orientation depicted in the Figures. For example, if the device in one of the figures is turned over, elements described as being on the “lower” side of other elements would then be oriented on “upper” sides of the other elements. The exemplary term “lower,” can therefore, encompass both an orientation of “lower” and “upper,” depending on the particular orientation of the figure. Similarly, if the device in one of the figures is turned over, elements described as “below” or “beneath” other elements would then be oriented “above” the other elements. The exemplary terms “below” or “beneath” can, therefore, encompass both an orientation of above and below.

“About” or “approximately” as used herein is inclusive of the stated value and means within an acceptable range of deviation for the particular value as determined by one of ordinary skill in the art, considering the measurement in question and the error associated with measurement of the particular quantity (i.e., the limitations of the measurement system). For example, “about” can mean within one or more standard deviations, or within $\pm 30\%$, 20%, 10%, 5% of the stated value.

Unless otherwise defined, all terms used herein (including technical and scientific terms) have the same meaning as commonly understood by those skilled in the art. It will be further understood that terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and will not be interpreted in an ideal or excessively formal sense unless clearly defined in the specification.

Exemplary embodiments are described herein with reference to cross section illustrations that are schematic illustrations of idealized embodiments. As such, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, embodiments described herein should not be construed as limited to the particular shapes of regions as illustrated herein but are to include deviations in shapes that result, for example, from manufacturing. For example, a region illustrated or described as flat may, typically, have rough and/or nonlinear features. Moreover, sharp angles that are illustrated may be rounded. Thus, the regions illustrated in the figures are schematic in nature and their shapes are not intended to illustrate the precise shape of a region and are not intended to limit the scope of the present claims.

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FIG. 1 is a plan view illustrating a pixel according to an exemplary embodiment. FIG. 2 is a cross-sectional view taken along line I-I' of FIG. 1. FIG. 3 is a cross-sectional view taken along line II-II' of FIG. 1. FIG. 4 is a cross-sectional view taken along line III-III' of FIG. 1.

A pixel, as illustrated in FIGS. 1 through 4, may include a first thin film transistor TFT1, a second thin film transistor TFT2, a third thin film transistor TFT3, a first storage line 751, a second storage line 752, a color filter 354, a first sub-pixel electrode PE1, a first extension electrode 181, a second sub-pixel electrode PE2, a second extension electrode 182, a third extension electrode 183, a common electrode 210, and a liquid crystal layer 333.

The first thin film transistor TFT1, as illustrated in FIG. 1, may include a first gate electrode GE1, a first semiconductor layer 311, a first source electrode SE1, and a first drain electrode DE1.

The second thin film transistor TFT2, as illustrated in FIG. 1, may include a second gate electrode GE2, a second semiconductor layer 312, a second source electrode SE2, and a second drain electrode DE2.

The third thin film transistor TFT3, as illustrated in FIG. 1, may include a third gate electrode GE3, a third semiconductor layer 313, a third source electrode SE3, and a third drain electrode DE3.

As illustrated in FIG. 1, a gate line GL may be disposed on a first substrate 301. In detail, the gate line GL may be disposed between a first sub-pixel region P1 and a second sub-pixel region P2 of the first substrate 301.

The gate line GL, as illustrated in FIG. 1, may include a line portion 411 and an electrode portion 412 having different line widths. In an exemplary embodiment, the electrode portion 412 may have a line width wider than that of the line portion 411. The line portion 411 and the electrode portion 412 may be unitary. The electrode portion 412 may include the aforementioned first gate electrode GE1, the second gate electrode GE2, and the third gate electrode GE3.

Although not illustrated, the gate line GL may have a connection portion, for example, an end portion thereof, which is greater than another portion thereof in size, to be connected to another layer or an external driving circuit.

In an exemplary embodiment, the gate line GL may include at least one of an aluminum (Al) based metal such as Al or an Al alloy, a silver (Ag) based metal such as Ag or an Ag alloy, a copper (Cu) based metal such as Cu or an Cu alloy, and a molybdenum (Mo) based metal such as Mo or a Mo alloy. In an alternative exemplary embodiment, the gate line GL may include at least one of chromium (Cr), tantalum (Ta), and titanium (Ti), for example. In an exemplary embodiment, the gate line GL may have a multilayer structure including at least two conductive layers having different physical properties.

The first storage line 751 may be disposed on the first substrate 301. The first storage line 751 may extend along at least one of sides of the first sub-pixel electrode PE1. In an exemplary embodiment, as illustrated in FIG. 1, the first storage line 751 may have a shape enclosing the first sub-pixel electrode PE1, for example. In this instance, the first storage line 751 and the first sub-pixel electrode PE1 may or may not overlap one another. In a case in which the first storage line 751 and the first sub-pixel electrode PE1 overlap one another, a portion of the first storage line 751 and at least one of the sides of the first sub-pixel electrode PE1 may overlap one another.

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The first storage line 751 may receive an externally applied first storage voltage. In an exemplary embodiment, the first storage voltage may be a direct current ("DC") voltage, for example.

The first storage line 751 may include the same material and may have the same structure (multilayer structure) as those of the aforementioned gate line GL. In other words, the gate line GL and the first storage line 751 may be simultaneously provided in the same process.

The second storage line 752 may be disposed on the first substrate 301. The second storage line 752 may extend along at least one of sides of the second sub-pixel electrode PE2. In an exemplary embodiment, as illustrated in FIG. 1, the second storage line 752 may be disposed to be adjacent to at least one of the sides of the second sub-pixel electrode PE2, for example. In this instance, the second storage line 752 and the second sub-pixel electrode PE2 may or may not overlap one another. In a case in which the second storage line 752 and the second sub-pixel electrode PE2 overlap one another, a portion of the second storage line 752 and at least one of the sides of the second sub-pixel electrode PE2 may overlap one another.

The second storage line 752 and the first storage line 751 may be connected to one another.

The second storage line 752 may include the same material and may have the same structure (multilayer structure) as those of the aforementioned gate line GL. In other words, the gate line GL and the second storage line 752 may be simultaneously provided in the same process.

A gate insulating layer 310 may be disposed on the gate line GL, the first storage line 751, and the second storage line 752. In this instance, the gate insulating layer 310 may be disposed on an entire surface of the first substrate 301 on which the first storage line 751 and the second storage line 752 are disposed.

As illustrated in FIG. 4, a third contact hole CH3 through which the first storage line 751 is exposed may be defined in the gate insulating layer 310.

In an exemplary embodiment, the gate insulating layer 310 may include silicon nitride (SiN_x), silicon oxide (SiO_x), or the like, for example. In an exemplary embodiment, the gate insulating layer 310 may have a multilayer structure including at least two insulating layers having different physical properties.

The first, second, and third semiconductor layers 311, 312, and 313 may be disposed on the gate insulating layer 310. In this instance, the first semiconductor layer 311 may overlap the first gate electrode GE1, the second semiconductor layer 312 may overlap the second gate electrode GE2, and the third semiconductor layer 313 may overlap the third gate electrode GE3.

The first, second, and third semiconductor layers 311, 312, and 313 may be connected to one another.

In an exemplary embodiment, the first, second, and third semiconductor layers 311, 312, and 313 may include amorphous silicon, polycrystalline silicon, or the like, for example.

The second semiconductor layer 312 may include a plurality of divided semiconductor layers. In an exemplary embodiment, as illustrated in FIG. 1, the second semiconductor layer 312 may include a first divided semiconductor layer 312a disposed between a portion of the second source electrode SE2 and the second drain electrode DE2, and a second divided semiconductor layer 312b disposed between another portion of the second source electrode SE2 and the second drain electrode DE2, for example.

An ohmic contact layer **360** may be disposed on the first, second, and third semiconductor layers **311**, **312**, and **313**. In this instance, the ohmic contact layer **360** may be disposed between the semiconductor layer and the source electrode and between the semiconductor layer and the drain electrode. In other words, the ohmic contact layer **360** may not be disposed on the semiconductor layer corresponding to each channel region of the first, second, and third thin film transistors **TFT1**, **TFT2**, and **TFT3**. In detail, the ohmic contact layer **360** may be disposed between the first semiconductor layer **311** and the first source electrode **SE1**, between the first semiconductor layer **311** and the first drain electrode **DE1**, between the second semiconductor layer **312** and the second source electrode **SE2**, between the second semiconductor layer **312** and the second drain electrode **DE2**, between the third semiconductor layer **313** and the third source electrode **SE3**, and between the third semiconductor layer **313** and the third drain electrode **DE3**.

In an exemplary embodiment, the ohmic contact layer **360** may include silicide or n+ hydrogenated amorphous silicon doped with high concentration n-type impurities such as phosphorus.

The first source electrode **SE1** and the first drain electrode **DE1** included in the first thin film transistor **TFT1**, the second source electrode **SE2** and the second drain electrode **DE2** included in the second thin film transistor **TFT2**, and the third source electrode **SE3** and the third drain electrode **DE3** included in the third thin film transistor **TFT3** may be disposed on the ohmic contact layer **360**.

The first source electrode **SE1**, as illustrated in FIG. 1, may extend from the data line **DL** onto the first gate electrode **GE1** to be disposed on the first gate electrode **GE1** and the first semiconductor layer **311**. The first source electrode **SE1** may overlap the first gate electrode **GE1** and the first semiconductor layer **311**. The first source electrode **SE1** may further overlap the line portion **411**. In an exemplary embodiment, the first source electrode **SE1** may have one of a C shape, an inverted-C shape, a U shape, and an inverted-U shape. By way of example, FIG. 1 illustrates the first source electrode **SE1** having a U shape.

In an exemplary embodiment, the first source electrode **SE1** may include a refractory metal such as chromium (Cr), tantalum (Ta) and titanium (Ti) or an alloy thereof. In an exemplary embodiment, the first source electrode **SE1** may have a multilayer structure including a refractory metal layer and a low-resistance conductive layer. Examples of the multilayer structure may include a double-layer structure including a Cr or Mo (Mo alloy) lower layer and an Al (Al alloy) upper layer, and a triple-layer structure including a Mo (Mo alloy) lower layer, an Al (Al alloy) intermediate layer, and a Mo (Mo alloy) upper layer. Further, the first source electrode **SE1** may include various metals or conductive materials other than the aforementioned materials.

The first drain electrode **DE1** may be disposed on the first gate electrode **GE1** and the first semiconductor layer **311**. The first drain electrode **DE1** may overlap the first gate electrode **GE1**, the first semiconductor layer **311**, and the first extension electrode **181**. In this instance, the first drain electrode **DE1** may be connected to the first extension electrode **181** through the first contact hole **CH1**. The first drain electrode **DE1** may further overlap the line portion **411**.

The first drain electrode **DE1** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode

SE1. In other words, the first drain electrode **DE1** and the first source electrode **SE1** may be simultaneously provided in the same process.

The first gate electrode **GE1**, the first source electrode **SE1**, the first drain electrode **DE1**, the first semiconductor layer **311**, and the ohmic contact layer **360** may constitute the first thin film transistor **TFT1**. In this instance, a channel of the first thin film transistor **TFT1** may be disposed on a portion of the first semiconductor layer **311** between the first source electrode **SE1** and the first drain electrode **DE1**. In an exemplary embodiment, the portion of the first semiconductor layer **311** corresponding to the channel may have a thickness less than that of another portion of the first semiconductor layer **311**.

The second source electrode **SE2** may be electrically connected to the first source electrode **SE1**. To this end, the second source electrode **SE2** and the first source electrode **SE1** may be unitary. The second source electrode **SE2** may be disposed on the second gate electrode **GE2** and the second semiconductor layer **312**. The second source electrode **SE2** may overlap the second gate electrode **GE2** and the second semiconductor layer **312**. The second source electrode **SE2** may further overlap the line portion **411**. In an exemplary embodiment, the second source electrode **SE2** may have one of a C shape, an inverted-C shape, a U shape, and an inverted-U shape. By way of example, FIG. 1 illustrates the second source electrode **SE2** having an inverted-U shape. In other words, the second source electrode **SE2** may have an inverted shape with respect to the shape of the first source electrode **SE1**.

The second source electrode **SE2** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode **SE1**. In other words, the second source electrode **SE2** and the first source electrode **SE1** may be simultaneously provided in the same process.

The second drain electrode **DE2** may be disposed on the second gate electrode **GE2** and the second semiconductor layer **312**. The second drain electrode **DE2** may overlap the second gate electrode **GE2**, the second semiconductor layer **312**, and the second extension electrode **182**. In this instance, the second drain electrode **DE2** may be connected to the second extension electrode **182** through the second contact hole **CH2**. The second drain electrode **DE2** may further overlap the line portion **411**.

The second drain electrode **DE2** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode **SE1**. In other words, the second drain electrode **DE2** and the first source electrode **SE1** may be simultaneously provided in the same process.

The second gate electrode **GE2**, the second source electrode **SE2**, the second drain electrode **DE2**, the second semiconductor layer **312**, and the ohmic contact layer **360** may constitute the second thin film transistor **TFT2**. In this instance, a channel of the second thin film transistor **TFT2** may be disposed on a portion of the second semiconductor layer **312** between the second source electrode **SE2** and the second drain electrode **DE2**. In an exemplary embodiment, the portion of the second semiconductor layer **312** corresponding to the channel may have a thickness less than that of another portion of the second semiconductor layer **312**.

The third source electrode **SE3** may be electrically connected to the second drain electrode **DE2**. To this end, the third source electrode **SE3** and the second drain electrode **DE2** may be unitary. The third source electrode **SE3** may be disposed on the third gate electrode **GE3** and the third

semiconductor layer **313**. The third source electrode **SE3** may overlap the third gate electrode **GE3**, the third semiconductor layer **313**, and the second extension electrode **182**. The third source electrode **SE3** may further overlap the line portion **411**.

The third source electrode **SE3** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode **SE1**. In other words, the third source electrode **SE3** and the first source electrode **SE1** may be simultaneously provided in the same process.

The third drain electrode **DE3** may be disposed on the third gate electrode **GE3**, the third semiconductor layer **313** and the first storage line **751**. The third drain electrode **DE3** may overlap the third gate electrode **GE3**, the third semiconductor layer **313**, the first storage line **751**, and the third extension electrode **183**. In this instance, the third drain electrode **DE3** may be connected to the third extension electrode **183** through the third contact hole **CH3**. The third drain electrode **DE3** may further overlap the line portion **411**.

The third drain electrode **DE3** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode **SE1**. In other words, the third drain electrode **DE3** and the first source electrode **SE1** may be simultaneously provided in the same process.

The third gate electrode **GE3**, the third source electrode **SE3**, the third drain electrode **DE3**, the third semiconductor layer **313**, and the ohmic contact layer **360** may constitute the third thin film transistor **TFT3**. In this instance, a channel of the third thin film transistor **TFT3** may be disposed on a portion of the third semiconductor layer **313** between the third source electrode **SE3** and the third drain electrode **DE3**. In an exemplary embodiment, the portion of the third semiconductor layer **313** corresponding to the channel may have a thickness less than that of another portion of the third semiconductor layer **313**.

The data line **DL** may be disposed on the gate insulating layer **310**. Although not illustrated, the data line **DL** may have a connection portion, for example, an end portion thereof, which is greater than another portion thereof in size, to be connected to another layer or an external driving circuit.

The data line **DL** may intersect the gate line **GL** and the first storage line **751**. Although not illustrated, the data line **DL** may have a narrower line width at a position at which the data line **DL** and the gate line **GL** intersect one another than a line width of another portion of the data line **DL**. Similarly, the data line **DL** may have a narrower line width at a position at which the data line **DL** and the first or second storage line **751** or **752** intersect one another than a line width of another portion of the data line **DL**. Accordingly, a parasitic capacitance between the data line **DL** and the gate line **GL**, and a capacitance between the data line **DL** and the first or second storage line **751** or **752** may decrease. The data line **DL** may include the same material and may have the same structure (multilayer structure) as those of the aforementioned first source electrode **SE1**. In other words, the data line **DL** and the first source electrode **SE1** may be simultaneously provided in the same process.

A semiconductor layer **314** and an ohmic contact layer **364** may be disposed below the data line **DL**, the first, second, and third source electrodes **SE1** through **SE3**, and the first, second, and third drain electrodes **DE1**, **DE2**, and **DE3**. In an exemplary embodiment, as illustrated in FIG. 2, the semiconductor layer **314** and the ohmic contact layer **364**

that have substantially the same shape as that of the data line **DL**, the first, second, and third source electrodes **SE1**, **SE2**, and **SE3**, and the first, second, and third drain electrodes **DE1**, **DE2**, and **DE3**. The protection layer **320** may be disposed on an entire surface of the first substrate **301** which includes the data line **DL**, the first, second, and third source electrodes **SE1**, **SE2**, and **SE3**, and the first, second, and third drain electrodes **DE1**, **DE2**, and **DE3**. The protection layer **320** may serve to remove a step difference between components disposed between the protection layer **320** and the first substrate **301**, such as the aforementioned data line **DL**, the first, second, and third source electrodes **SE1**, **SE2**, and **SE3**, and the first, second, and third drain electrodes **DE1**, **DE2**, and **DE3**. In addition, the protection layer **320** may serve to protect the components of the first substrate **301**.

In an exemplary embodiment, the protection layer **320** may include an inorganic insulating material such as SiN_x or SiO_x . In a case that the protection layer **320** includes such an inorganic insulating material, an inorganic insulating material having photosensitivity and a dielectric constant of about 4.0 may be used, for example. In a case in which the protection layer **320** has a double-layer structure including a lower inorganic layer and an upper organic layer, an excellent insulating property of an organic layer may be achieved and damage to an exposed portion of the third semiconductor layer **313** may be significantly reduced. In an exemplary embodiment, the protection layer **320** may have a thickness greater than or equal to about 5000 angstroms (\AA), and more particularly, in a range of about 6000 \AA to about 8000 \AA , for example.

The first, second, and third contact holes **CH1**, **CH2**, and **CH3** penetrating through a portion of the protection layer **320** may be defined, and portions of the first, second, and third source electrodes **SE1**, **SE2**, and **SE3** may be exposed through the first, second, and third contact holes **CH1**, **CH2**, and **CH3**, respectively.

The first sub-pixel electrode **PE1** may be disposed on the protection layer **320**. In detail, the first sub-pixel electrode **PE1** may be disposed on the protection layer **320** of the first sub-pixel region **P1**. A description pertaining to the first sub-pixel electrode **PE1** will be provided hereinbelow with reference to FIG. 5.

FIG. 5 is a view illustrating the first sub-pixel electrode **PE1** of FIG. 1.

The first sub-pixel electrode **PE1**, as illustrated in FIG. 5, may include a stem electrode **613** and a plurality of branch electrodes **601a**, **601b**, **601c**, and **601d**. The stem electrode **613** and the plurality of branch electrodes **601a**, **601b**, **601c**, and **601d** may be unitary.

The stem electrode **613** may divide the first sub-pixel region **P1** into a plurality of domains. In an exemplary embodiment, the stem electrode **613** may include a horizontal portion **611** and a vertical portion **612** that intersect one another. The horizontal portion **611** may divide the first sub-pixel region **P1** into two domains. The vertical portion **612** may divide each of the two divided domains further into two smaller domains. That is, the first sub-pixel region **P1** may be divided into four domains A, B, C, and D by the stem electrode **613** including the horizontal portion **611** and the vertical portion **612**, for example. However, the invention is not limited thereto, and the first sub-pixel region **P1** may include a different number of the domains.

The stem electrode **613** may divide the first sub-pixel region **P1** into a plurality of domains. In an exemplary embodiment, the stem electrode **613** may include a horizontal portion **611** and a vertical portion **612** that intersect one another. The horizontal portion **611** may divide the first sub-pixel region **P1** into two domains. The vertical portion **612** may divide each of the two divided domains further into two smaller domains. That is, the first sub-pixel region **P1** may be divided into four domains A, B, C, and D by the stem electrode **613** including the horizontal portion **611** and the vertical portion **612**, for example. However, the invention is not limited thereto, and the first sub-pixel region **P1** may include a different number of the domains.

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The branch electrodes **601a**, **601b**, **601c**, and **601d** may include first, second, third, and fourth branch electrodes **601a**, **601b**, **601c**, and **601d** extending from the stem electrode **613** into different directions from one another. In other words, the first, second, third, and fourth branch electrodes **601a**, **601b**, **601c**, and **601d** may extend from the stem electrode **613** onto the domains A, B, C, and D, respectively. In an exemplary embodiment, the first branch electrode **601a** may be disposed in the first domain A, the second branch electrode **601b** may be disposed in the second domain B, the third branch electrode **601c** may be disposed in the third domain C, and the fourth branch electrode **601d** may be disposed in the fourth domain D, for example.

The first branch electrode **601a** and the second branch electrode **601b** may be symmetrical to one another with reference to the vertical portion **612**, and the third branch electrode **601c** and the fourth branch electrode **601d** may be symmetrical to one another with reference to the vertical portion **612**. In addition, the first branch electrode **601a** and the fourth branch electrode **601d** may be symmetrical to one another with reference to the horizontal portion **611**, and the second branch electrode **601b** and the third branch electrode **601c** may be symmetrical to one another with reference to the horizontal portion **611**.

As the first domain A may include a plurality of first branch electrodes **601a**, the plurality of first branch electrodes **601a** may be arranged in parallel to one another. In this instance, at least one of the first branch electrodes **601a** may extend from a side of a horizontal portion **611** in the first domain A in a diagonal direction with respect to the side of the horizontal portion **611**. The remainder of the first branch electrodes **601a** may extend from a side of the vertical portion **612** in the first domain A in a diagonal direction with respect to the side of the vertical portion **612**.

As the second domain B may include a plurality of second branch electrodes **601b**, the plurality of second branch electrodes **601b** may be arranged in parallel to one another. In this instance, at least one of the second branch electrodes **601b** may extend from a side of the horizontal portion **611** in the second domain B in a diagonal direction with respect to the side of the horizontal portion **611**. The remainder of the second branch electrodes **601b** may extend from a side of the vertical portion **612** in the second domain B in a diagonal direction with respect to the side of the vertical portion **612**.

As the third domain C may include a plurality of third branch electrodes **601c**, the plurality of third branch electrodes **601c** may be arranged in parallel to one another. In this instance, at least one of the third branch electrodes **601c** may extend from a side of the horizontal portion **611** in the third domain C in a diagonal direction with respect to the side of the horizontal portion **611**. The remainder of the third branch electrodes **601c** may extend from a side of the vertical portion **612** in the third domain C in a diagonal direction with respect to the side of the vertical portion **612**.

As the fourth domain D may include a plurality of fourth branch electrodes **601d**, the plurality of fourth branch electrodes **601d** may be arranged in parallel to one another. In this instance, at least one of the fourth branch electrodes **601d** may extend from a side of the horizontal portion **611** in the fourth domain D in a diagonal direction with respect to the side of the horizontal portion **611**. The remainder of the fourth branch electrodes **601d** may extend from a side of the vertical portion **612** in the fourth domain D in a diagonal direction with respect to the side of the vertical portion **612**.

The aforementioned stem electrode **613** may further include a first connector **614a** and a second connector **614b**.

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The first connector **614a** may be connected to one end of the horizontal portion **611**, and the second connector **614b** may be connected to the other end of the horizontal portion **611**. The first connector **614a** and the second connector **614b** may be aligned in parallel to the vertical portion **612**. The first connector **614a** and the second connector **614b** may be integrally provided with the stem electrode **613**.

An end portion of at least one of the first branch electrodes **601a** in the first domain A and an end portion of at least one of the fourth branch electrodes **601d** in the fourth domain D may be connected to one another by the second connector **614b**. Similarly, an end portion of at least one of the second branch electrodes **601b** in the second domain B and an end portion of at least one of the third branch electrodes **601c** in the third domain C may be connected to one another by the first connector **614a**.

The second sub-pixel electrode PE2 may be disposed on the protection layer **320**. In detail, the second sub-pixel electrode PE2 may be disposed on the protection layer **320** of the second sub-pixel region P2.

The second sub-pixel electrode PE2 may have substantially the same structure as that of the first sub-pixel electrode PE1. In other words, the second sub-pixel electrode PE2 may include a stem electrode by which the second sub-pixel region P2 is divided into a plurality of domains, and a plurality of branch electrodes extending from the stem electrode onto the respective domains. In addition, the second sub-pixel electrode PE2 may further include a first connector and a second connector. Since the stem electrode, the branch electrode, the first connector, and the second connector included in the second sub-pixel electrode PE2 are the same as those included in the aforementioned first sub-pixel electrode PE1, reference may be made to analogous features described in FIG. 5.

The third extension electrode **183** may be disposed on the protection layer **320**. The third extension electrode **183** may overlap the first storage line **751** and the third drain electrode DE3. The third extension electrode **183** may be connected to the first storage line **751** and the third drain electrode DE3 through the third contact hole CH3.

The third extension electrode **183** may include the same material forming the aforementioned first sub-pixel electrode PE1.

Although not illustrated, a display device according to the illustrated exemplary embodiment may further include a protection line. The protection line may be disposed on the protection layer **320**. In detail, the protection line may be disposed on a portion of the protection layer **320** on the data line DL. In other words, the protection line may overlap the data line DL. In an exemplary embodiment, the protection line may have a line width wider than that of the data line DL.

In an exemplary embodiment, the protection line may include the same material forming the aforementioned first sub-pixel electrode PE1. In this instance, the protection line may be connected to the third extension electrode **183**. In other words, the protection line and the third extension electrode **183** may be unitary.

A common voltage may be applied to the protection line. According to exemplary embodiments, a voltage having a level lower than or equal to that of the common voltage may be applied to the protection line.

Although not illustrated, a lower alignment layer may be disposed on the first sub-pixel electrode PE1, the first extension electrode **181**, the second sub-pixel electrode PE2, the second extension electrode **182**, the protection line, the third extension electrode **183**, and the protection layer **320**.

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In an exemplary embodiment, the lower alignment layer may be a homeotropic alignment layer or may include a photo-reactive material.

A black matrix 376 may be disposed on the second substrate 302. In detail, the black matrix 376 may be disposed on a portion of the second substrate 302 aside from a portion thereof corresponding to a pixel region P including the first sub-pixel region P1 and the second sub-pixel region P2. In an alternative exemplary embodiment, the black matrix 376 may be disposed on the first substrate 301 rather than the second substrate 302.

The color filter 354 may be disposed in the pixel region P. In an exemplary embodiment, the color filter 354 may include a red color filter, a green color filter, and a blue color filter, for example. In an alternative exemplary embodiment, the color filter 354 may be disposed on the first substrate 301 rather than the second substrate 302.

An overcoat layer 722 may be disposed on the black matrix 376 and the color filter 354. In this instance, the overcoat layer 722 may be disposed on an entire surface of the second substrate 302 which includes the black matrix 376 and the color filter 354.

The overcoat layer 722 may serve to remove a step difference between components disposed between the overcoat layer 722 and the second substrate 302, such as the aforementioned black matrix 376 and the color filter 354. In addition, the overcoat layer 722 may serve to prevent external leakage of a dye forming the color filter 354.

A common electrode 210 may be disposed on the overcoat layer 722. In this instance, the common electrode 210 may be disposed on an entire surface of the first substrate 301 which includes the overcoat layer 722. In an alternative exemplary embodiment, the common electrode 210 may be disposed on the overcoat layer 722 corresponding to the first sub-pixel region P1 and the second sub-pixel region P2.

A common voltage may be applied to the common electrode 210. In an exemplary embodiment, the aforementioned first storage voltage and the second storage voltage may have the same level as that of the common voltage. In an alternative exemplary embodiment, the first storage voltage, the second storage voltage, and the common voltage may have different levels.

In an exemplary embodiment, the common electrode 210 may include the same material forming the aforementioned first sub-pixel electrode PE1.

Although not illustrated, an upper alignment layer may be disposed on the common electrode 210 and the overcoat layer 722. In an exemplary embodiment, the upper alignment layer may be a homeotropic alignment layer and may be an alignment layer which is photo-aligned using a photopolymerization material, for example.

A liquid crystal layer 333 may be interposed between the first and second substrates 301 and 302. In an exemplary embodiment, the liquid crystal layer 333 may include a photopolymerization material, and such a photopolymerization material may be a reactive monomer or a reactive mesogen.

When surfaces of the first substrate 301 and the second substrate 302 that face one another are defined as upper surfaces of the corresponding substrates, respectively, and surfaces of the first substrate 301 and the second substrate 302 opposite to the upper surfaces thereof are defined as lower surfaces of the corresponding substrates, respectively, an upper polarizer may further be disposed on the lower surface of the first substrate 301, and a lower polarizer may further be disposed on the lower surface of the second substrate 302.

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A transmission axis of the upper polarizer may be perpendicular to a transmission axis of the lower polarizer, and thus one of the transmission axes and the line portion 411 of the gate line GL may be aligned in parallel to one another. In an exemplary embodiment, the display device may only include one of the upper polarizer and the lower polarizer.

FIG. 6 is an equivalent circuit schematic of the pixel illustrated in FIG. 1.

The pixel, as illustrated in FIG. 6, may include the first thin film transistor TFT1, a first liquid crystal capacitor Clc1, a first storage capacitor Cst1, the second thin film transistor TFT2, a second liquid crystal capacitor Clc2, a second storage capacitor Cst2, and the third thin film transistor TFT3.

The first thin film transistor TFT1 may be controlled based on a gate signal from the gate line GL, and may be connected between the data line DL and the first sub-pixel electrode PE1. The first thin film transistor TFT1 may be turned on by a gate high voltage of the gate signal to thereby apply a data signal from the data line DL to the first sub-pixel electrode PE1.

The first liquid crystal capacitor Clc1 may be connected between the first sub-pixel electrode PE1 and the common electrode 210 opposing one another. As described above, a common voltage Vcom may be applied to the common electrode 210.

The first storage capacitor Cst1 may be connected between the first sub-pixel electrode PE1 and the first storage line 751 opposing one another. A storage voltage Vsct may be applied to the first storage line 751. In an exemplary embodiment, the storage voltage Vsct may have the same level as that of the common voltage Vcom.

The second thin film transistor TFT2 may be controlled based on a gate signal from the gate line GL, and may be connected between the data line DL and the second sub-pixel electrode PE2. The second thin film transistor TFT2 may be turned on by a gate high voltage of the gate signal to thereby apply a data signal from the data line DL to the second sub-pixel electrode PE2.

The second liquid crystal capacitor Clc2 may be connected between the second sub-pixel electrode PE2 and the common electrode 210 opposing one another.

The second storage capacitor Cst2 may be connected between the second sub-pixel electrode PE2 and the second storage line 752 opposing one another. A storage voltage Vsct may be applied to the second storage line 752. In an exemplary embodiment, the storage voltage Vsct may have the same level as that of the common voltage Vcom.

The third thin film transistor TFT3 may be controlled based on a gate signal from the gate line GL, and may be connected between the second sub-pixel electrode PE2 and the first storage line 751. The third thin film transistor TFT3 may be turned on by a gate high voltage of the gate signal to thereby apply a data signal from the second sub-pixel electrode PE2 to the first storage line 751.

The pixel illustrated in FIG. 6 may operate as follows.

When a gate signal is applied to the gate line GL, data voltages transmitted to the data line DL may be applied to the first sub-pixel electrode PE1 and the second sub-pixel electrode PE2 through the first thin film transistor TFT1 and the second thin film transistor TFT2, respectively.

The data voltage transmitted through the first thin film transistor TFT1 may be totally applied to the first sub-pixel electrode PE1 whereas only a portion of the data voltage transmitted through the second thin film transistor TFT2 may be applied to the second sub-pixel electrode PE2 due to the third thin film transistor TFT3. Accordingly, a luminance

of the first sub-pixel region P1 in which the first sub-pixel electrode PE1 is disposed may be higher than a luminance of the second sub-pixel region P2 in which the second sub-pixel electrode PE2 is disposed.

In detail, when a gate signal is applied to the gate line GL, a data voltage applied to the second source electrode SE2 of the second thin film transistor TFT2 may pass through a channel to be transmitted to the second drain electrode DE2 of the second thin film transistor TFT2. A portion of the data voltage transmitted to the second drain electrode DE2 of the second thin film transistor TFT2 may be applied to the second sub-pixel electrode PE2, and another portion of the data voltage may be discharged to the first storage line 751 through the third thin film transistor TFT3.

Since the data voltage is divided based on a resistance ratio between the second thin film transistor TFT2 and the third thin film transistor TFT3, when properties of the second thin film transistor TFT2 and the third thin film transistor TFT3 satisfy a condition of Equation 1 provided below, a ratio (voltage ratio) between the data voltage applied to the first sub-pixel electrode PE1 and the data voltage applied to the second sub-pixel electrode PE2 may hardly vary. In other words, a range of the variation in the voltage ratio may be significantly reduced. Hereinafter, the range of the variation in the voltage ratio will be referred to as a "voltage ratio distribution range".

$$W_TFT3/W_TFT2 = \Delta W_TFT3/\Delta W_TFT2 \quad [\text{Equation 1}]$$

In Equation 1, W_TFT3 denotes a channel width of the third thin film transistor TFT3, W_TFT2 denotes a channel width of the second thin film transistor TFT2, ΔW_TFT3 denotes a channel width variation of the third thin film transistor TFT3, and ΔW_TFT2 denotes a channel width variation of the second thin film transistor TFT2. As used herein, the channel width may refer to an effective channel width.

According to Equation 1, when a ratio between the channel width W_TFT3 of the third thin film transistor TFT3 and the channel width W_TFT2 of the second thin film transistor TFT2 is the same as a ratio between the channel width variation ΔW_TFT3 of the third thin film transistor TFT3 and the channel width variation ΔW_TFT2 of the second thin film transistor TFT2, the voltage ratio distribution range may be significantly reduced.

To significantly reduce the voltage ratio distribution range, the second thin film transistor TFT2 and the third thin film transistor TFT3 may have a relationship as will be described hereinbelow with reference to FIGS. 7 through 10.

FIG. 7 is a view illustrating an example of a structure of the second thin film transistor TFT2 and the third thin film transistor TFT3 of FIG. 1.

As illustrated in FIG. 7A, the second thin film transistor TFT2 may include a plurality of divided channel regions. In an exemplary embodiment, the plurality of divided channel regions may include a first channel region 701 and a second channel region 702 that are divided from one another, for example.

A second source electrode SE2 of the second thin film transistor TFT2 may include two protrusions. A second drain electrode DE2 may be disposed between the two protrusions.

The first channel region 701 and the second channel region 702 of the second thin film transistor TFT2 may be defined by the second source electrode SE2 and the second drain electrode DE2. In detail, the first channel region 701 may correspond to a first divided semiconductor layer 312a between one of the protrusions of the second source elec-

trode SE2 and the second drain electrode DE2, and the second channel region 702 may correspond to a second divided semiconductor layer 312b between the other of the protrusions of the second source electrode SE2 and the second drain electrode DE2.

Respective end portions of the second source electrode SE2 and the second drain electrode DE2 facing one another may have a linear shape.

As illustrated in FIG. 7B, the third thin film transistor TFT3 may include a single channel region 700.

The channel region 700 of the third thin film transistor TFT3 may be defined by a third source electrode SE3 and a third drain electrode DE3. In detail, the channel region 700 may correspond to a third semiconductor layer 313 between the third source electrode SE3 and the third drain electrode DE3.

Respective end portions of the third source electrode SE3 and the third drain electrode DE3 facing one another may have a linear shape. A length of the end portions may be the same.

The second thin film transistor TFT2 may have a greater channel region than that of the third thin film transistor TFT3. In other words, a total area of the channel region included in the second thin film transistor TFT2 may be greater than that included in the third thin film transistor TFT3. In an exemplary embodiment, as illustrated in FIGS. 7A and 7B, a total area calculated by a sum of an area of the first channel region 701 of the second thin film transistor TFT2 and an area of the second channel region 702 of the second thin film transistor TFT2 may be greater than an area of the channel region 700 of the third thin film transistor TFT3, for example.

The second thin film transistor TFT2 may include a channel region having the same shape and area as a channel region of the third thin film transistor TFT3. In other words, one of the channel regions included in the second thin film transistor TFT2 and one of the channel regions included in the third thin film transistor TFT3 may have the same shape and area. In an exemplary embodiment, as illustrated in FIGS. 7A and 7B, the first channel region 701 of the second thin film transistor TFT2 may have the same shape and area as that of the channel region 700 of the third thin film transistor TFT3, for example. Also, the second channel region 702 of the second thin film transistor TFT2 may have the same shape and area as those of the channel region 700 of the third thin film transistor TFT3. In other words, when the second thin film transistor TFT2 includes a plurality of divided channel regions, the channel regions of the second thin film transistor TFT2 may each have the same shape and area as those of the channel region 700 of the third thin film transistor TFT3. In particular, a channel width Wa of the first channel region 701 included in the second thin film transistor TFT2 and a channel width Wb of the channel region 700 included in the third thin film transistor TFT3 may be the same, and a channel length La of the first channel region 701 included in the second thin film transistor TFT2 and a channel length Lb of the channel region 700 included in the third thin film transistor TFT3 may be the same. Similarly, a channel width Wa of the second channel region 702 included in the second thin film transistor TFT2 and the channel width Wb of the channel region 700 included in the third thin film transistor TFT3 may be the same, and a channel length La of the second channel region 702 included in the second thin film transistor TFT2 and the channel length Lb of the channel region 700 included in the third thin film transistor TFT3 may be the same.

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As the plurality of channel regions included in the second thin film transistor TFT2 each have the same shape and area as those of the channel region 700 included in the third thin film transistor TFT3, a ratio between the channel width of the third thin film transistor TFT3 and the channel width of the second thin film transistor TFT2 may be substantially the same as a ratio between the channel width variation of the third thin film transistor TFT3 and the channel width variation of the second thin film transistor TFT2. Accordingly, the voltage ratio distribution range may be significantly reduced.

In FIGS. 7A and 7B, a ratio between a total channel width of the second thin film transistor TFT2 and a total channel width of the third thin film transistor TFT3 may be 2:1, for example.

FIGS. 8A and 8B are views illustrating another example of the structure of the second thin film transistor TFT2 and the third thin film transistor TFT3 of FIG. 1.

As illustrated in FIG. 8A, the second thin film transistor TFT2 may include a plurality of divided channel regions. In an exemplary embodiment, the plurality of channel regions may include a first channel region 701 and a second channel region 702 that are divided from one another, for example.

A second source electrode SE2 of the second thin film transistor TFT2 may include two protrusions. A second drain electrode DE2 may be disposed between the two protrusions.

The first channel region 701 and the second channel region 702 of the second thin film transistor TFT2 may be defined by the second source electrode SE2 and the second drain electrode DE2. In detail, the first channel region 701 may correspond to a first divided semiconductor layer 312a between one of the protrusions of the second source electrode SE2 and the second drain electrode DE2, and the second channel region 702 may correspond to a second divided semiconductor layer 312b between the other of the protrusions of the second source electrode SE2 and the second drain electrode DE2.

Respective end portions of the second source electrode SE2 and the second drain electrode DE2 facing one another may have a curved shape. A length of the end portions may be the same. In addition, the end portion of the second source electrode SE2 and the end portion of the second drain electrode DE2 may each include a plurality of sides having different lengths. In this instance, a side included in the end portion of the second source electrode SE2 and a side included in the end portion of the second drain electrode DE2 may be disposed to correspond to one another and may have different lengths. In an exemplary embodiment, as illustrated in FIG. 8A, in the second source electrode SE2 and the second drain electrode DE2 defining the first channel region 701, the end portion of the second source electrode SE2 and the end portion of the second drain electrode DE2 facing one another may each include three sides having different lengths and facing different directions, for example. In this instance, a short diagonal side included in the end portion of the second source electrode SE2 may face a long diagonal side included in the end portion of the second drain electrode DE2, a vertical side included in the end portion of the second source electrode SE2 may face a vertical side included in the end portion of the second drain electrode DE2, and a long diagonal side included in the end portion of the second source electrode SE2 may face a short diagonal side included in the end portion of the second drain electrode DE2.

As illustrated in FIG. 8B, the third thin film transistor TFT3 may include a single channel region 700.

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The channel region 700 of the third thin film transistor TFT3 may be defined by a third source electrode SE3 and a third drain electrode DE3. In detail, the channel region 700 may correspond to a third semiconductor layer 313 between the third source electrode SE3 and the third drain electrode DE3.

Respective end portions of the third source electrode SE3 and the third drain electrode DE3 facing one another may have a curved shape. In this instance, a length of the end portions may be the same. In addition, the end portion of the third source electrode SE3 and the end portion of the third drain electrode DE3 may each include a plurality of sides having different lengths. In this instance, a side included in the end portion of the third source electrode SE3 and a side included in the end portion of the third drain electrode DE3 may be disposed to correspond to one another and may have different lengths. In an exemplary embodiment, as illustrated in FIG. 8B, in the third source electrode SE3 and the third drain electrode DE3 defining the channel region 700, the end portion of the third source electrode SE3 and the end portion of the third drain electrode DE3 facing one another may each include three sides having different lengths and facing different directions, for example. In this instance, a short diagonal side included in the end portion of the third source electrode SE3 may face a long diagonal side included in the end portion of the third drain electrode DE3, a vertical side included in the end portion of the third source electrode SE3 may face a vertical side included in the end portion of the third drain electrode DE3, and a long diagonal side included in the end portion of the third source electrode SE3 may face a short diagonal side included in the end portion of the third drain electrode DE3.

The second thin film transistor TFT2 and the third thin film transistor TFT3 illustrated in FIGS. 8A and 8B may have substantially the same structure as that of the second thin film transistor TFT2 and the third thin film transistor TFT3 described with reference to FIGS. 7A and 7B. In other words, as illustrated in FIGS. 8A and 8B, the plurality of channel regions included in the second thin film transistor TFT2 may each have the same shape and area as those of the channel region included in the third thin film transistor TFT3. In an exemplary embodiment, a channel width W_a of the first channel region 701 included in the second thin film transistor TFT2 and a channel width W_b of the channel region 700 included in the third thin film transistor TFT3 may be the same, and a channel length L_a of the first channel region 701 included in the second thin film transistor TFT2 and a channel length L_b of the channel region 700 included in the third thin film transistor TFT3 may be the same, for example. Similarly, a channel width W_a of the second channel region 702 included in the second thin film transistor TFT2 and the channel width W_b of the channel region 700 included in the third thin film transistor TFT3 may be the same, and a channel length L_a of the second channel region 702 included in the second thin film transistor TFT2 and the channel length L_b of the channel region 700 included in the third thin film transistor TFT3 may be the same.

In FIGS. 8A and 8B, a ratio between a total channel width of the second thin film transistor TFT2 and a total channel width of the third thin film transistor TFT3 may be 2:1.

FIGS. 9A and 9B are views illustrating still another example of the structure of the second thin film transistor TFT2 and the third thin film transistor TFT3 of FIG. 1.

As illustrated in FIG. 9A, the second thin film transistor TFT2 may include a plurality of spaced-apart channel regions. In an exemplary embodiment, the plurality of

channel regions may include a first channel region **701**, a second channel region **702**, and a third channel region **703** that are divided from one another, for example.

A second source electrode **SE2** of the second thin film transistor **TFT2** may include two protrusions. A second drain electrode **DE2** of the second thin film transistor **TFT2** may include two protrusions. One of the protrusions of the second source electrode **SE2** may be disposed between the two protrusions of the second drain electrode **DE2**. One of the protrusions of the second drain electrode **DE2** may be disposed between the two protrusions of the second source electrode **SE2**.

The first channel region **701**, the second channel region **702**, and the third channel region **703** of the second thin film transistor **TFT2** may be defined by the second source electrode **SE2** and the second drain electrode **DE2**. In detail, the first channel region **701** may correspond to a first divided semiconductor layer **312a** between one of the protrusions of the second source electrode **SE2** and one of the protrusions of the second drain electrode **DE2**, the second channel region **702** may correspond to a second divided semiconductor layer **312b** between one of the protrusions of the second source electrode **SE2** and the other of the protrusions of the second drain electrode **DE2**, and the third channel region **703** may correspond to a third divided semiconductor layer **312c** between the other of the protrusions of the second source electrode **SE2** and the other of the protrusions of the second drain electrode **DE2**.

As illustrated in FIG. **9B**, the third thin film transistor **TFT3** may include a single channel region **700**.

The second thin film transistor **TFT2** and the third thin film transistor **TFT3** illustrated in FIGS. **9A** and **9B** may have substantially the same structure as that of the second thin film transistor **TFT2** and the third thin film transistor **TFT3** described with reference to FIGS. **8A** and **8B**. In other words, as illustrated in FIGS. **9A** and **9B**, the plurality of channel regions included in the second thin film transistor **TFT2** may have the same shape and area as those of the channel region included in the third thin film transistor **TFT3**. In an exemplary embodiment, in FIGS. **9A** and **9B**, a channel width W_a of the first channel region **701** included in the second thin film transistor **TFT2** and a channel width W_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the first channel region **701** included in the second thin film transistor **TFT2** and a channel length L_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, for example. Similarly, a channel width W_a of the second channel region **702** included in the second thin film transistor **TFT2** and the channel width W_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the second channel region **702** included in the second thin film transistor **TFT2** and the channel length L_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same. Similarly, a channel width W_a of the third channel region **703** included in the second thin film transistor **TFT2** and the channel width W_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the third channel region **703** included in the second thin film transistor **TFT2** and the channel length L_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same.

In FIGS. **9A** and **9B**, a ratio between a total channel width of the second thin film transistor **TFT2** and a total channel width of the third thin film transistor **TFT3** may be 3:1.

FIGS. **10A** and **10B** are views illustrating yet another example of the structure of the second thin film transistor **TFT2** and the third thin film transistor **TFT3** of FIG. **1**.

As illustrated in FIG. **10A**, the second thin film transistor **TFT2** may include a plurality of spaced-apart channel regions. In an exemplary embodiment, the plurality of channel regions may include a first channel region **701**, a second channel region **702**, a third channel region **703**, and a fourth channel region **704** that are divided from one another, for example.

A second source electrode **SE2** of the second thin film transistor **TFT2** may include three protrusions. A second drain electrode **DE2** of the second thin film transistor **TFT2** may include two protrusions.

One of the protrusions of the second drain electrode **DE2** may be disposed between one and another of the protrusions of the second source electrode **SE2**. The other of the protrusions of the second drain electrode **DE2** may be disposed between another and the other of the protrusions of the second source electrode **SE2**.

The first channel region **701**, the second channel region **702**, the third channel region **703**, and the fourth channel region **704** of the second thin film transistor **TFT2** may be defined by the second source electrode **SE2** and the second drain electrode **DE2**. In detail, the first channel region **701** may correspond to a first divided semiconductor layer **312a** between one of the protrusions of the second source electrode **SE2** and one of the protrusions of the second drain electrode **DE2**, the second channel region **702** may correspond to a second divided semiconductor layer **312b** between another of the protrusions of the second source electrode **SE2** and one of the protrusions of the second drain electrode **DE2**, the third channel region **703** may correspond to a third divided semiconductor layer **312c** between another of the protrusions of the second source electrode **SE2** and the other of the protrusions of the second drain electrode **DE2**, and the fourth channel region **704** may correspond to a fourth divided semiconductor layer **312d** between the other of the protrusions of the second source electrode **SE2** and the other of the protrusions of the second drain electrode **DE2**.

As illustrated in FIG. **10B**, the third thin film transistor **TFT3** may include a single channel region **700**.

The second thin film transistor **TFT2** and the third thin film transistor **TFT3** illustrated in FIGS. **10A** and **10B** may have substantially the same structure as that of the second thin film transistor **TFT2** and the third thin film transistor **TFT3** described with reference to FIGS. **8A** and **8B**. In other words, as illustrated in FIGS. **10A** and **10B**, the plurality of channel regions included in the second thin film transistor **TFT2** may each have the same shape and area as those of the channel region included in the third thin film transistor **TFT3**. In an exemplary embodiment, in FIGS. **10A** and **10B**, a channel width W_a of the first channel region **701** included in the second thin film transistor **TFT2** and a channel width W_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the first channel region **701** included in the second thin film transistor **TFT2** and a channel length L_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, for example. Similarly, a channel width W_a of the second channel region **702** included in the second thin film transistor **TFT2** and the channel width W_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the second channel region **702** included in the second thin film transistor **TFT2** and the channel length L_b of the channel region **700** included in the third thin film transistor **TFT3** may be the same, and a channel length L_a of the second channel region **701** included in the second thin film transistor **TFT2** and the channel length L_b of the channel region **700** included in the third thin film transistor **TFT3**

may be the same. Similarly, a channel width W_a of the third channel region **703** included in the second thin film transistor TFT2 and the channel width W_b of the channel region **700** included in the third thin film transistor TFT3 may be the same, and a channel length L_a of the third channel region **703** included in the second thin film transistor TFT2 and the channel length L_b of the channel region **700** included in the third thin film transistor TFT3 may be the same. Similarly, a channel width W_a of the fourth channel region **704** included in the second thin film transistor TFT2 and the channel width W_b of the channel region **700** included in the third thin film transistor TFT3 may be the same, and a channel length L_a of the fourth channel region **704** included in the second thin film transistor TFT2 and the channel length L_b of the channel region **700** included in the third thin film transistor TFT3 may be the same.

In FIGS. **10A** and **10B**, a ratio between a total channel width of the second thin film transistor TFT2 and a total channel width of the third thin film transistor TFT3 may be 4:1.

The third thin film transistor TFT3 may include the number of channel regions “ n ” times (“ n ” being a natural number) greater than the number of channel regions included in the second thin film transistor TFT2. In an exemplary embodiment, the number of channel regions included in the third thin film transistor TFT3 may be “ n ” times greater than the number of channel regions included in the second thin film transistor TFT2, for example.

FIG. **11** is a view illustrating effects of the exemplary embodiment.

Referring to FIG. **11**, a second thin film transistor TFT2' may be a conventional second thin film transistor TFT2 equivalent to the second thin film transistor TFT2 according to the exemplary embodiment, and the conventional second thin film transistor TFT2' may include a single channel region having a different area than that of the third thin film transistor TFT3 according to the exemplary embodiment in size.

In FIG. **11**, W_{min} denotes a minimum channel width of the third thin film transistor TFT3 according to the exemplary embodiment, the conventional TFT2', and the second thin film transistor TFT2 according to the exemplary embodiment, and W_{max} denotes a maximum channel width of the third thin film transistor TFT3 according to the exemplary embodiment, the conventional TFT2', and the second thin film transistor TFT2 according to the exemplary embodiment. ΔW denotes a variation range between the minimum channel width and the maximum channel width.

When a channel width (total channel width) of the second thin film transistor TFT2 and a channel width (total channel width) of the third thin film transistor TFT3 that are provided in FIG. **11** have a ratio, for example, 2:1 (the ratio of the channel width of the second thin film transistor TFT2 to the channel width of the third thin film transistor TFT3 is 2), as previously described with reference to FIGS. **8A** and **8B**, a simulation result with regard to the structure of the second thin film transistor TFT2 according to the exemplary embodiment indicates 2.18 ($=2.64/1.21$), which is substantially approximate to the ratio in FIGS. **8A** and **8B**. A simulation result with regard to the structure of the conventional second thin film transistor TFT2' indicates 0.86 ($=1.04/1.21$), which is significantly lower than 2, which is the ratio obtained in the second thin film transistor TFT2 according to the exemplary embodiment.

As set forth above, according to one or more exemplary embodiments, in the display device, the plurality of channel regions included in the second thin film transistor may each

have the same shape and area as those of the channel region included in the third thin film transistor. Accordingly, the resistance ratio between the transistors may be readily predicted, thus resulting in the simplified design and manufacture of the transistor.

In addition, the source electrode and the drain electrode may include the same number of protrusions. Accordingly, the voltage deviation caused by the varying polarity of the data voltage may be significantly reduced.

From the foregoing, it will be appreciated that various embodiments in accordance with the disclosure have been described herein for purposes of illustration, and that various modifications may be made without departing from the scope and spirit of the teachings. Accordingly, the various embodiments disclosed herein are not intended to be limiting of the true scope and spirit of the teachings. Various features of the above described and other embodiments can be mixed and matched in any manner, to produce further embodiments consistent with the invention.

What is claimed is:

1. A liquid crystal display device comprising:
 - a first substrate comprising a gate line and a data line;
 - a second substrate opposing the first substrate;
 - a liquid crystal layer between the first substrate and the second substrate;
 - a first sub-pixel electrode in a first sub-pixel region of the first substrate;
 - a second sub-pixel electrode in a second sub-pixel region of the first substrate;
 - a first transistor connected to the gate line, the data line, and the first sub-pixel electrode;
 - a second transistor connected to the gate line, the first transistor, and the second sub-pixel electrode; and
 - a third transistor connected to the gate line, the second sub-pixel electrode, and a storage line,
 wherein the second transistor comprises a plurality of divided channel regions;
- wherein one of the plurality of divided channel regions of the second transistor has the same shape and area as a shape and an area of the channel region of the third transistor.
2. The liquid crystal display device of claim 1, wherein a number of the plurality of divided channel regions of second transistor is “ n ” times (“ n ” being a natural number) greater than a number of channel regions of one the first and third transistors.
3. The liquid crystal display device of claim 2, wherein a number of the plurality of divided channel regions of the second transistor is “ n ” times greater than a number of channel regions of the third transistor.
4. The liquid crystal display device of claim 1, wherein a number of channel regions of the first transistor is equal to a number of channel regions of the third transistor.
5. The liquid crystal display device of claim 1, wherein a source electrode and a drain electrode included in the one of the first, second and third transistors have a same number of protrusions.
6. The liquid crystal display device of claim 1, wherein a total area of the plurality of divided channel regions included in the second transistor is greater than the area of the channel region included in the third transistor.
7. The liquid crystal display device of claim 1, wherein respective end portions of a source electrode and a drain electrode facing one another of at least one of the first, second, and third transistors have a curved shape.

8. The liquid crystal display device of claim 7, wherein the end portion of the source electrode and the end portion of the drain electrode each include a plurality of sides having different lengths.

9. The liquid crystal display device of claim 8, wherein the end portion of the source electrode and the end portion of the drain electrode each include sides having the different lengths at respective corresponding positions.

10. The liquid crystal display device of claim 7, wherein the end portion of the source electrode has a same length as a length of the end portion of the drain electrode facing one another.

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